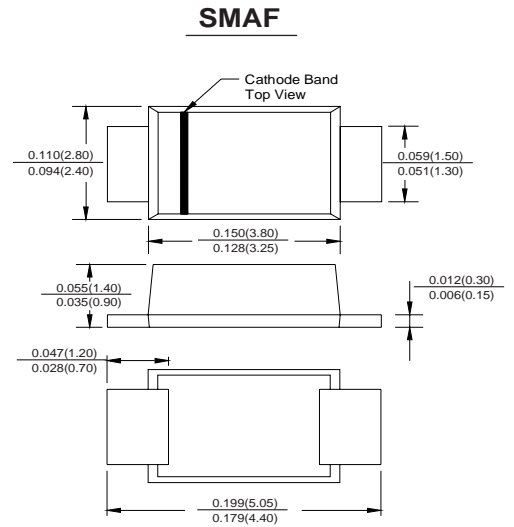


FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Easy to pick and place
- Fast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

- Case: SMAF
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 27mg 0.00086oz



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	RS1AF	RS1BF	RS1DF	RS1GF	RS1JF	RS1KF	RS1MF	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_a = 65\text{ }^\circ\text{C}$	$I_{F(AV)}$	1							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	30							A
Maximum Instantaneous Forward Voltage at 1 A	V_F	1.3							V
Maximum DC Reverse Current $T_a = 25\text{ }^\circ\text{C}$ at Rated DC Blocking Voltage $T_a = 125\text{ }^\circ\text{C}$	I_R	5 100							μA
Maximum Reverse Recovery Time ¹⁾	t_{rr}	150			250		500		ns
Typical Junction Capacitance ²⁾	C_j	15							pF
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150							$^\circ\text{C}$

1) Measured with $I_F = 0.5\text{ A}$, $I_R = 1\text{ A}$, $I_{rr} = 0.25\text{ A}$

2) Measured at 1MHz and applied reverse voltage of 4V D.C

Fig.1 Forward Current Derating Curve

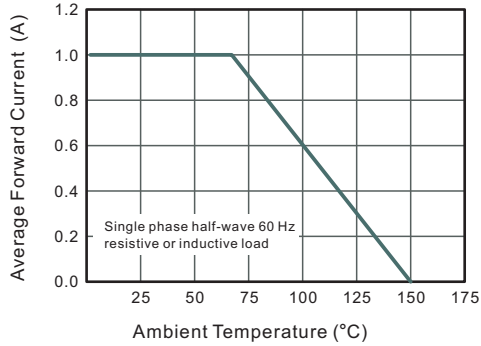


Fig.2 Typical Reverse Characteristics

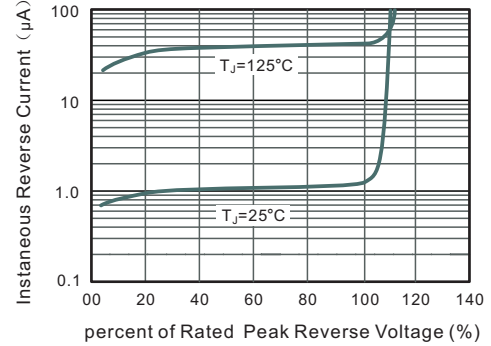


Fig.3 Typical Instantaneous Forward Characteristics

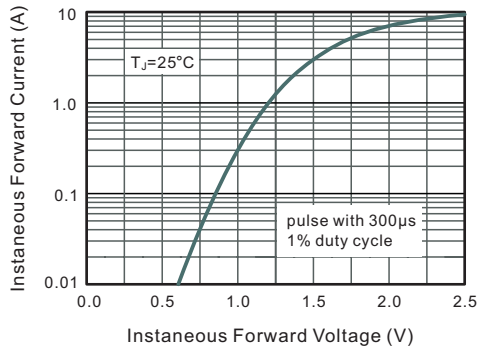


Fig.4 Typical Junction Capacitance

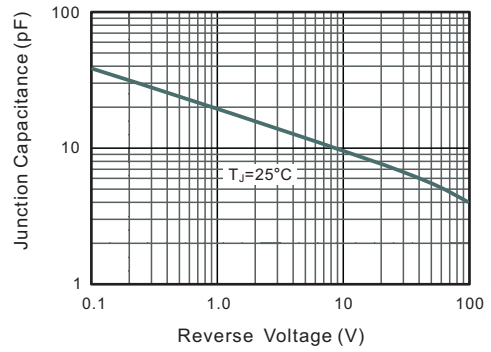


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

